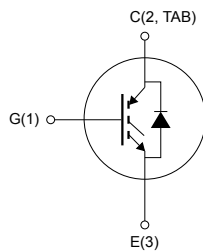


Trench gate field-stop, 650 V, 40 A, high-speed HB series IGBT in a TO-247 long leads package



TO-247 long leads



NG1E3C2T



Features

- Maximum junction temperature: $T_J = 175\text{ }^\circ\text{C}$
- High speed switching series
- Minimized tail current
- Low saturation voltage: $V_{CE(sat)} = 1.6\text{ V (typ.) @ } I_C = 40\text{ A}$
- Tight parameter distribution
- Safe paralleling
- Positive $V_{CE(sat)}$ temperature coefficient
- Low thermal resistance
- Co-packaged protection diode

Applications

- Power factor correction (PFC)

Description

This device is an IGBT developed using an advanced proprietary trench gate field-stop structure. The device is part of the new HB series of IGBTs, which represents an optimum compromise between conduction and switching loss to maximize the efficiency of any frequency converter. Furthermore, the slightly positive $V_{CE(sat)}$ temperature coefficient and very tight parameter distribution result in safer paralleling operation.

Product status link

[STGWA40HP65FB](#)

Product summary

| | |
|-------------------|-------------------|
| Order code | STGWA40HP65FB |
| Marking | G40HP65FB |
| Package | TO-247 long leads |
| Packing | Tube |

1 Electrical ratings

Table 1. Absolute maximum ratings

| Symbol | Parameter | Value | Unit |
|----------------|--|------------|------|
| V_{CES} | Collector-emitter voltage ($V_{GE} = 0$ V) | 650 | V |
| I_C | Continuous collector current at $T_C = 25$ °C | 80 | A |
| | Continuous collector current at $T_C = 100$ °C | 40 | |
| $I_{CP}^{(1)}$ | Pulsed collector current | 160 | |
| V_{GE} | Gate-emitter voltage | ±20 | V |
| | Transient gate-emitter voltage | ±30 | |
| $I_F^{(2)}$ | Continuous forward current at $T_C = 25$ °C | 5 | A |
| | Continuous forward current at $T_C = 100$ °C | 5 | |
| $I_{FP}^{(3)}$ | Pulsed forward current | 10 | |
| P_{TOT} | Total power dissipation at $T_C = 25$ °C | 283 | W |
| T_{STG} | Storage temperature range | -55 to 150 | °C |
| T_J | Operating junction temperature range | -55 to 175 | |

1. Pulse width is limited by maximum junction temperature.
2. Limited by wires.
3. Pulsed forward current.

Table 2. Thermal data

| Symbol | Parameter | Value | Unit |
|------------|--|-------|------|
| R_{thJC} | Thermal resistance junction-case IGBT | 0.53 | °C/W |
| | Thermal resistance junction-case diode | 5 | |
| R_{thJA} | Thermal resistance junction-ambient | 50 | |

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 3. Static characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|---------------|--------------------------------------|--|------|------|-----------|---------------|
| $V_{(BR)CES}$ | Collector-emitter breakdown voltage | $V_{GE} = 0\text{ V}, I_C = 2\text{ mA}$ | 650 | | | V |
| $V_{CE(sat)}$ | Collector-emitter saturation voltage | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}$ | | 1.6 | 2.0 | V |
| | | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 125\text{ °C}$ | | 1.7 | | |
| | | $V_{GE} = 15\text{ V}, I_C = 40\text{ A}, T_J = 175\text{ °C}$ | | 1.8 | | |
| V_F | Forward on-voltage | $I_F = 5\text{ A}$ | | 2 | | V |
| | | $I_F = 5\text{ A}, T_J = 125\text{ °C}$ | | 1.85 | | |
| | | $I_F = 5\text{ A}, T_J = 175\text{ °C}$ | | 1.75 | | |
| $V_{GE(th)}$ | Gate threshold voltage | $V_{CE} = V_{GE}, I_C = 1\text{ mA}$ | 5 | 6 | 7 | V |
| I_{CES} | Collector cut-off current | $V_{GE} = 0\text{ V}, V_{CE} = 650\text{ V}$ | | | 25 | μA |
| I_{GES} | Gate-emitter leakage current | $V_{CE} = 0\text{ V}, V_{GE} = \pm 20\text{ V}$ | | | ± 250 | nA |

Table 4. Dynamic characteristics

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------|------------------------------|---|------|------|------|------|
| C_{ies} | Input capacitance | $V_{CE} = 25\text{ V}, f = 1\text{ MHz}, V_{GE} = 0\text{ V}$ | - | 5412 | - | pF |
| C_{oes} | Output capacitance | | - | 198 | - | |
| C_{res} | Reverse transfer capacitance | | - | 107 | - | |
| Q_g | Total gate charge | $V_{CC} = 520\text{ V}, I_C = 40\text{ A},$ | - | 210 | - | nC |
| Q_{ge} | Gate-emitter charge | $V_{GE} = 0\text{ to }15\text{ V}$ | - | 39 | - | |
| Q_{gc} | Gate-collector charge | (see Figure 28. Gate charge test circuit) | - | 82 | - | |

Table 5. Switching characteristics (inductive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|-----------------|---------------------------|---|------|------|------|---------------|
| $t_{d(off)}$ | Turn-off delay time | $V_{CC} = 400\text{ V}$, $I_C = 40\text{ A}$, | - | 142 | - | ns |
| t_f | Current fall time | $V_{GE} = 15\text{ V}$, $R_G = 5\ \Omega$ | - | 27 | - | ns |
| $E_{off}^{(1)}$ | Turn-off switching energy | (see Figure 27. Test circuit for inductive load switching) | - | 363 | - | μJ |
| $t_{d(off)}$ | Turn-off delay time | $V_{CC} = 400\text{ V}$, $I_C = 40\text{ A}$, | - | 141 | - | ns |
| t_f | Current fall time | $V_{GE} = 15\text{ V}$, $R_G = 5\ \Omega$, | - | 61 | - | ns |
| $E_{off}^{(1)}$ | Turn-off switching energy | $T_J = 175\text{ }^\circ\text{C}$ (see Figure 27. Test circuit for inductive load switching) | - | 764 | - | μJ |

1. Including the tail of the collector current.

Table 6. Diode switching characteristics (inductive load)

| Symbol | Parameter | Test conditions | Min. | Typ. | Max. | Unit |
|--------------|--|---|------|------|------|------------------------|
| t_{rr} | Reverse recovery time | | - | 140 | - | ns |
| Q_{rr} | Reverse recovery charge | $I_F = 5\text{ A}$, $V_R = 400\text{ V}$, | - | 21 | - | nC |
| I_{rrm} | Reverse recovery current | $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$ | - | 6.6 | - | A |
| di_{rr}/dt | Peak rate of fall of reverse recovery current during t_b | (see Figure 27. Test circuit for inductive load switching) | - | 430 | - | $\text{A}/\mu\text{s}$ |
| E_{rr} | Reverse recovery energy | | - | 1.6 | - | μJ |
| t_{rr} | Reverse recovery time | | - | 200 | - | ns |
| Q_{rr} | Reverse recovery charge | $I_F = 5\text{ A}$, $V_R = 400\text{ V}$, | - | 47.3 | - | nC |
| I_{rrm} | Reverse recovery current | $V_{GE} = 15\text{ V}$, $di/dt = 1000\text{ A}/\mu\text{s}$, | - | 9.6 | - | A |
| di_{rr}/dt | Peak rate of fall of reverse recovery current during t_b | $T_J = 175\text{ }^\circ\text{C}$ (see Figure 27. Test circuit for inductive load switching) | - | 428 | - | $\text{A}/\mu\text{s}$ |
| E_{rr} | Reverse recovery energy | | - | 3.2 | - | μJ |

2.1 Electrical characteristics (curves)

Figure 1. Power dissipation vs case temperature

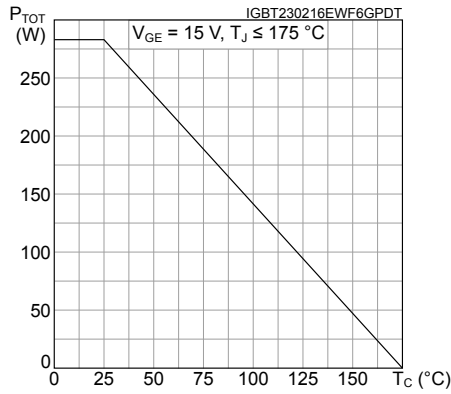


Figure 2. Collector current vs case temperature

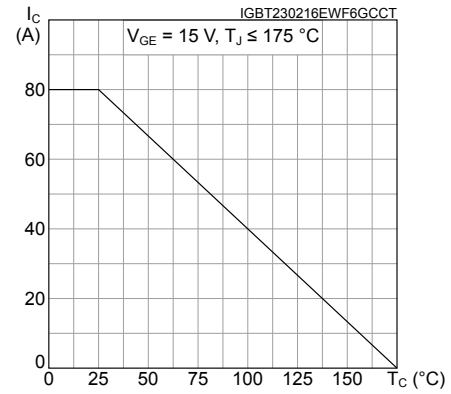


Figure 3. Output characteristics (T_J = 25°C)

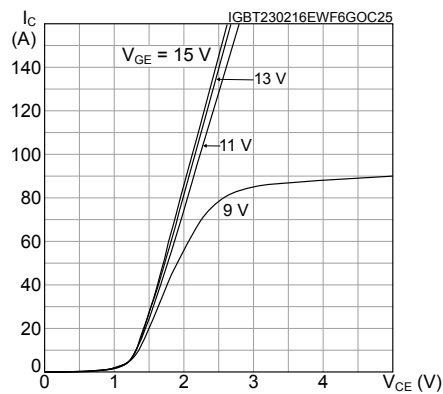


Figure 4. Output characteristics (T_J = 175°C)

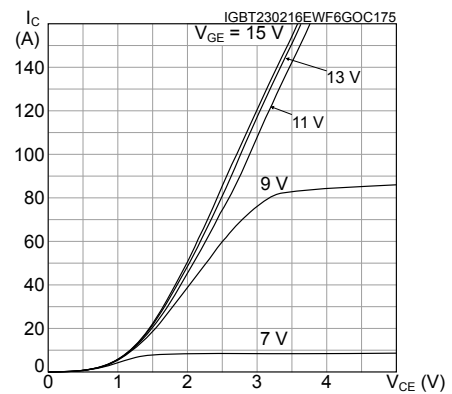


Figure 5. V_{CE(sat)} vs junction temperature

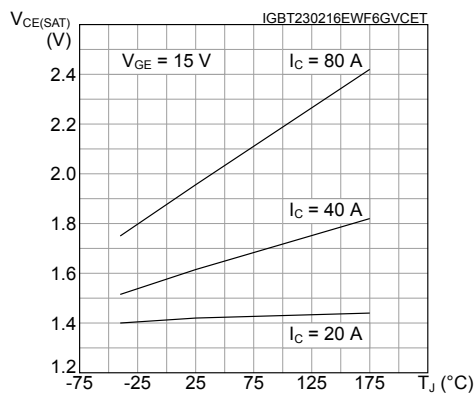


Figure 6. V_{CE(sat)} vs collector current

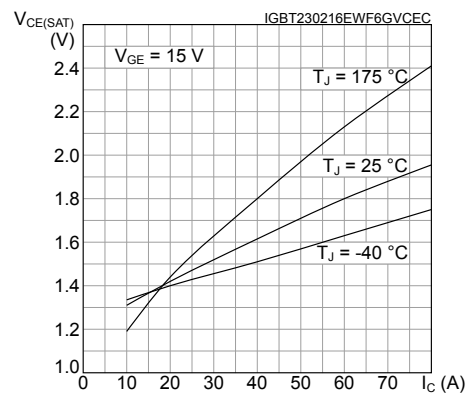


Figure 7. Collector current vs switching frequency

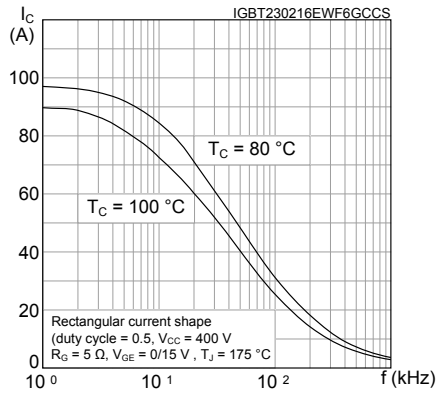


Figure 8. Forward bias safe operating area

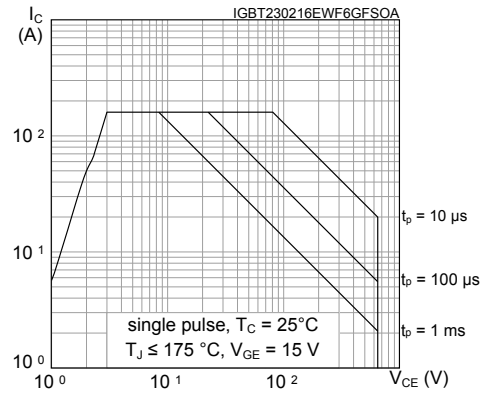


Figure 9. Transfer characteristics

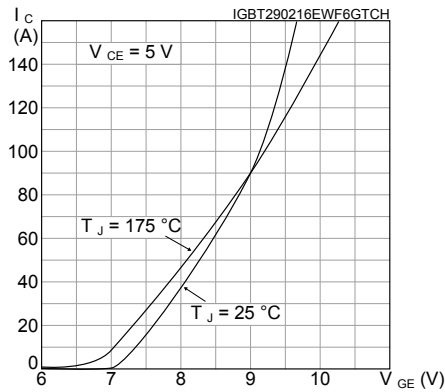


Figure 10. Diode V_F vs forward current

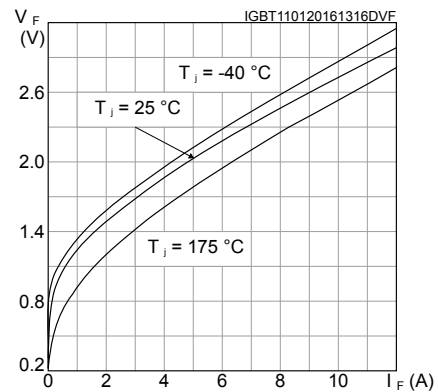


Figure 11. Normalized $V_{GE(th)}$ vs junction temperature

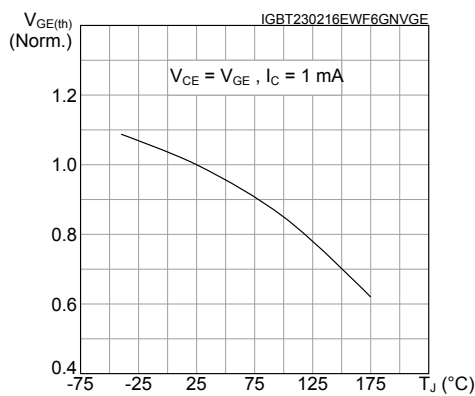


Figure 12. Normalized $V_{(BR)CES}$ vs junction temperature

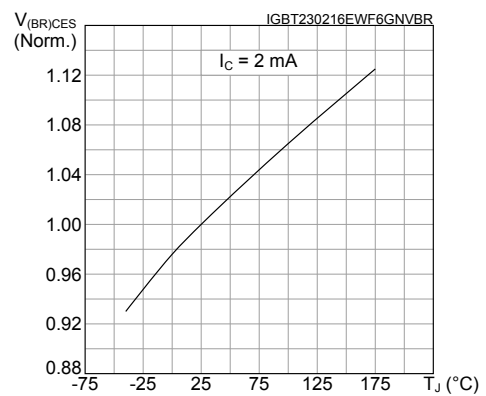


Figure 13. Capacitance variations

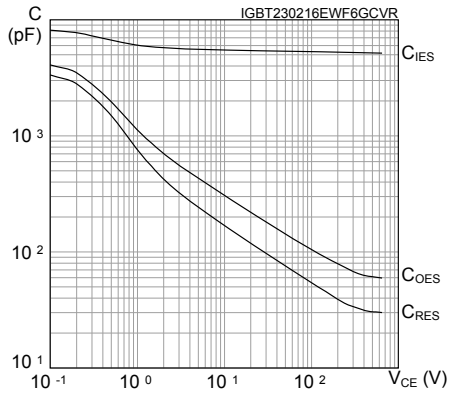


Figure 14. Gate charge vs gate-emitter voltage

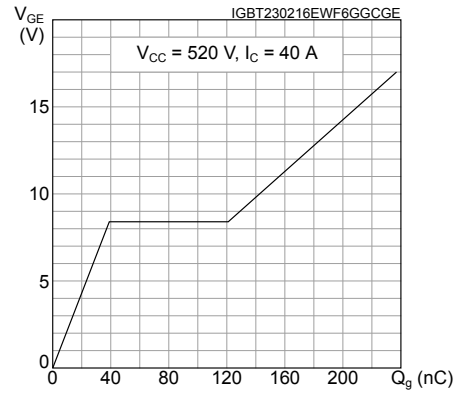


Figure 15. Switching energy vs collector current

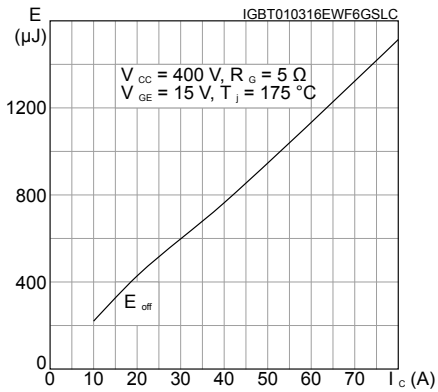


Figure 16. Switching energy vs gate resistance

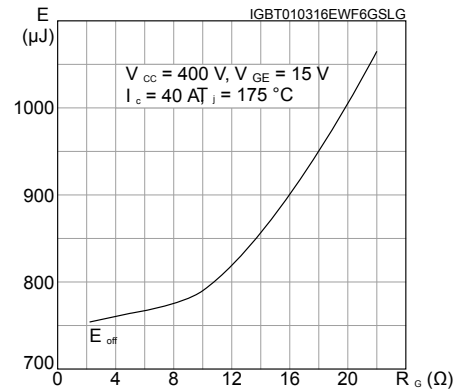


Figure 17. Switching energy vs temperature

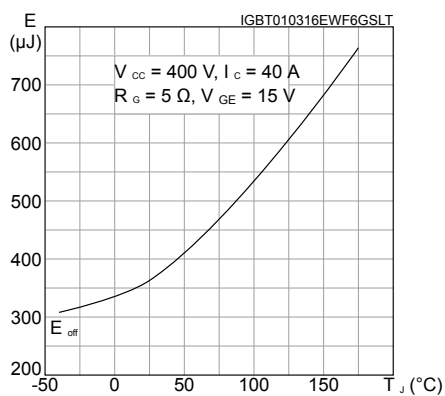


Figure 18. Switching energy vs collector emitter voltage

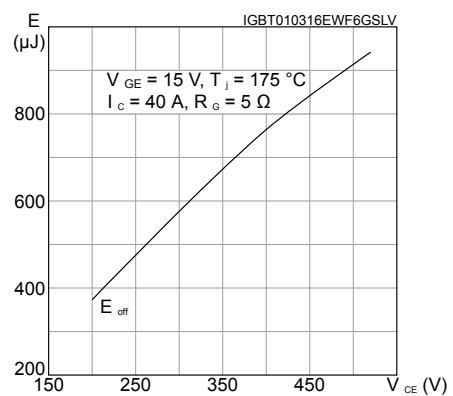


Figure 19. Switching times vs collector current

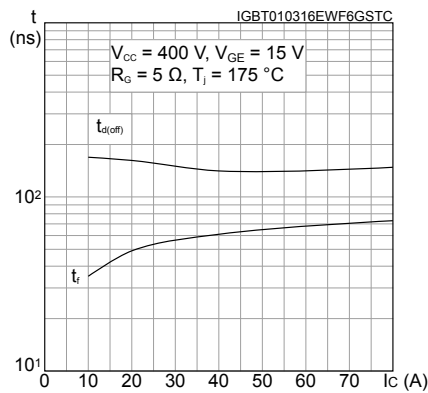


Figure 20. Switching times vs gate resistance

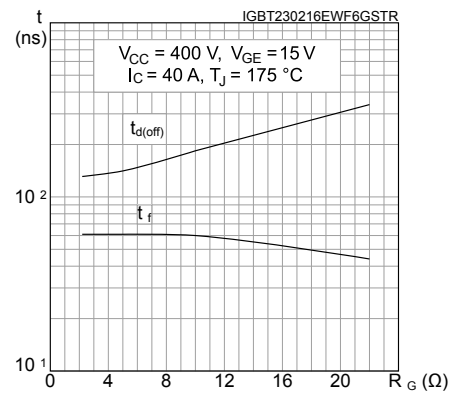


Figure 21. Reverse recovery current vs diode current slope

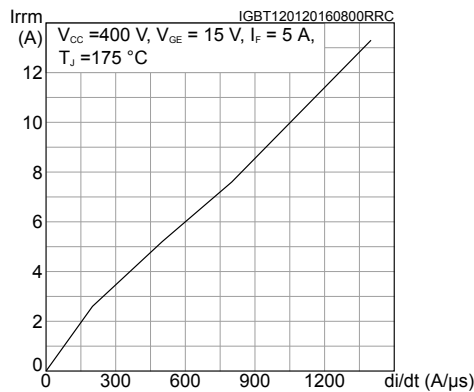


Figure 22. Reverse recovery time vs diode current slope

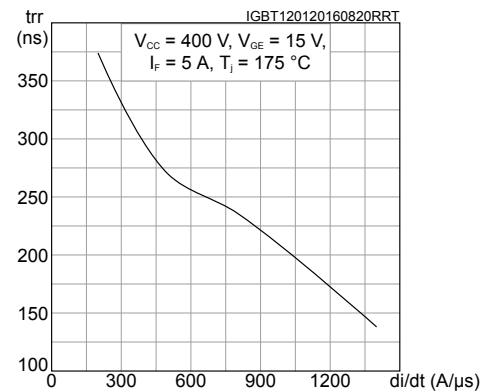


Figure 23. Reverse recovery charge vs diode current slope

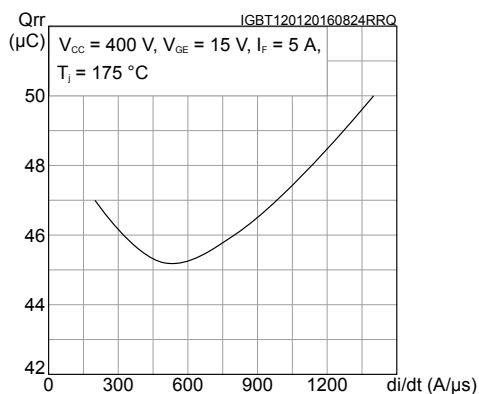


Figure 24. Reverse recovery energy vs diode current slope

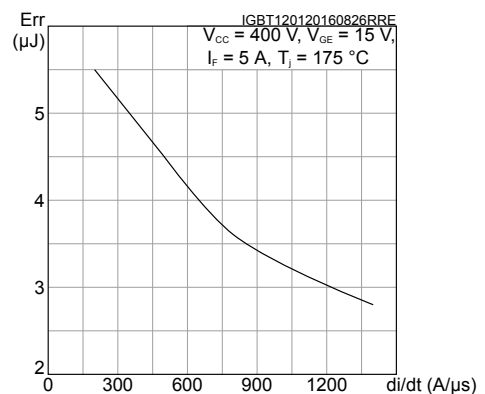


Figure 25. Thermal impedance

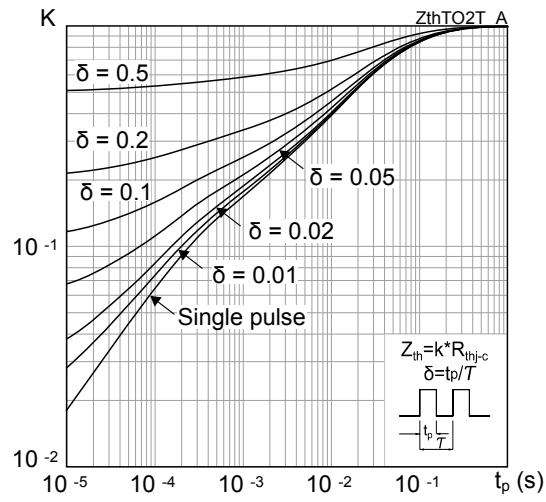
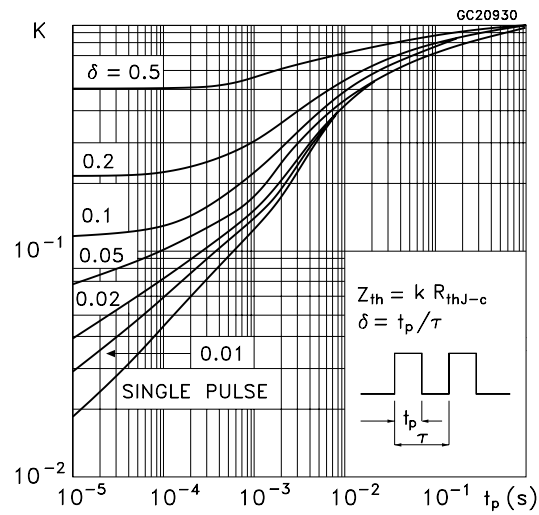


Figure 26. Thermal impedance for diode

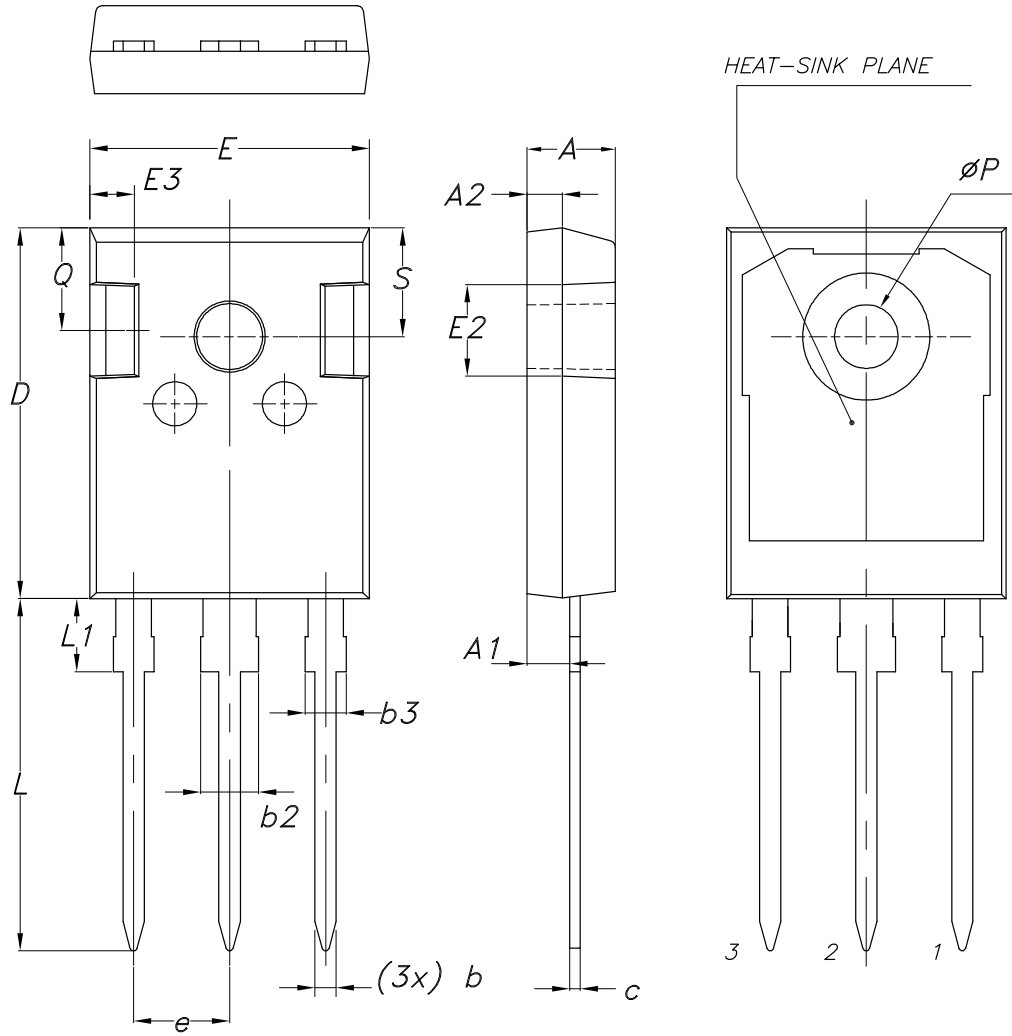


4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

4.1 TO-247 long leads package information

Figure 30. TO-247 long leads package outline



8463846_2_F

Table 7. TO-247 long leads package mechanical data

| Dim. | mm | | |
|------|-------|-------|-------|
| | Min. | Typ. | Max. |
| A | 4.90 | 5.00 | 5.10 |
| A1 | 2.31 | 2.41 | 2.51 |
| A2 | 1.90 | 2.00 | 2.10 |
| b | 1.16 | | 1.26 |
| b2 | | | 3.25 |
| b3 | | | 2.25 |
| c | 0.59 | | 0.66 |
| D | 20.90 | 21.00 | 21.10 |
| E | 15.70 | 15.80 | 15.90 |
| E2 | 4.90 | 5.00 | 5.10 |
| E3 | 2.40 | 2.50 | 2.60 |
| e | 5.34 | 5.44 | 5.54 |
| L | 19.80 | 19.92 | 20.10 |
| L1 | | | 4.30 |
| P | 3.50 | 3.60 | 3.70 |
| Q | 5.60 | | 6.00 |
| S | 6.05 | 6.15 | 6.25 |

Revision history

Table 8. Document revision history

| Date | Version | Changes |
|-------------|---------|----------------|
| 20-Jun-2019 | 1 | First release. |

Contents

| | | |
|------------|--|-----------|
| 1 | Electrical ratings | 2 |
| 2 | Electrical characteristics | 3 |
| 2.1 | Electrical characteristics (curves) | 5 |
| 3 | Test circuits | 10 |
| 4 | Package information | 11 |
| 4.1 | TO-247 long leads package information | 11 |
| | Revision history | 14 |

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